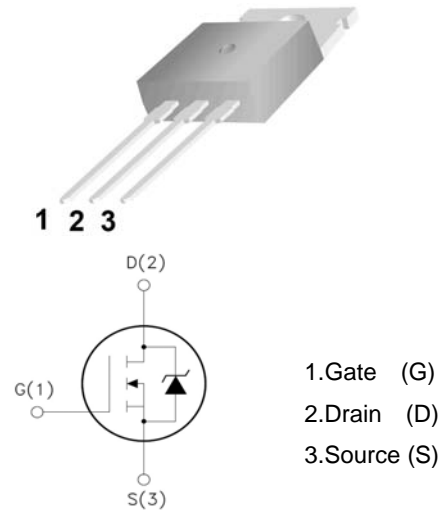


## XXW230N04

### Features:

- Low Intrinsic Capacitances.
- Excellent Switching Characteristics.
- Extended Safe Operating Area.
- Unrivalled Gate Charge :Qg= 190nC (Typ.).
- BV<sub>DSS</sub>=40V, I<sub>D</sub>=230A
- R<sub>DS(on)</sub> : 2.3mΩ (Typ.) @V<sub>G</sub>=10V
- 100% Avalanche Tested

TO-220



### Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Maximum	Unit
V <sub>DSS</sub>	Drain-to-Source Voltage	40	V
V <sub>GSS</sub>	Gate-to-Source Voltage	±20	V
I <sub>D</sub> <sup>3</sup>	Continuous Drain Current	T <sub>C</sub> =25°C	230
		T <sub>C</sub> =100°C	162
I <sub>DP</sub> <sup>4</sup>	Pulsed Drain Current	T <sub>C</sub> =25°C	800
I <sub>AS</sub> <sup>5</sup>	Avalanche Current		33
EAS <sup>5</sup>	Avalanche energy		1.5
PD	Maximum Power Dissipation	T <sub>C</sub> =25°C	285
		T <sub>C</sub> =100°C	145
T <sub>J</sub> , T <sub>STG</sub>	Junction & Storage Temperature Range	-55~175	°C

### Thermal Characteristics

Symbol	Parameter	Typical	Unit
R <sub>θjc</sub>	Thermal Resistance-Junction to Case	0.52	°C/W
R <sub>θja</sub>	Thermal Resistance-Junction to Ambient	62.5	

**Electrical Characteristics** (TA=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ	Max.	Unit
<b>Static Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	—	—	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V	—	—	1	uA
		T <sub>J</sub> =125°C	—	—	10	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	3	4	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	—	—	±100	nA
R <sub>DS(on)</sub> <sup>1</sup>	Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =60A	—	2.3	4	mΩ
			—	—	—	
<b>Diode Characteristics</b>						
V <sub>SD</sub> <sup>1</sup>	Diode Forward Voltage	I <sub>SD</sub> =60A, V <sub>GS</sub> =0V	—	—	1.3	V
I <sub>S</sub> <sup>3</sup>	Diode Continuous Forward Current		—	—	250	A
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =60A,	—	37	—	nS
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/us	—	62	—	nC
<b>Dynamic Characteristics<sup>2</sup></b>						
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, Frequency=1MHz	—	1	—	Ω
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V Frequency=1MHz	—	7000	—	pF
C <sub>oss</sub>	Output Capacitance		—	1850	—	
C <sub>rss</sub>	Reverse Transfer Capacitance		—	675	—	
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, I <sub>D</sub> =60A, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω	—	35	—	nS
t <sub>r</sub>	Turn-On Rise Time		—	20	—	
t <sub>d(off)</sub>	Turn-Off Delay Time		—	45	—	
t <sub>f</sub>	Turn-Off Fall Time		—	62	—	
<b>Gate Charge Characteristics<sup>2</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =32V, V <sub>GS</sub> =10V I <sub>D</sub> =60A	—	190	—	nC
Q <sub>gs</sub>	Gate-to-Source Charge		—	30	—	
Q <sub>gd</sub>	Gate-to-Drain Charge		—	80	—	

Note: 1: Pulse test; pulse width ≤ 300us, duty cycle ≤ 2%.

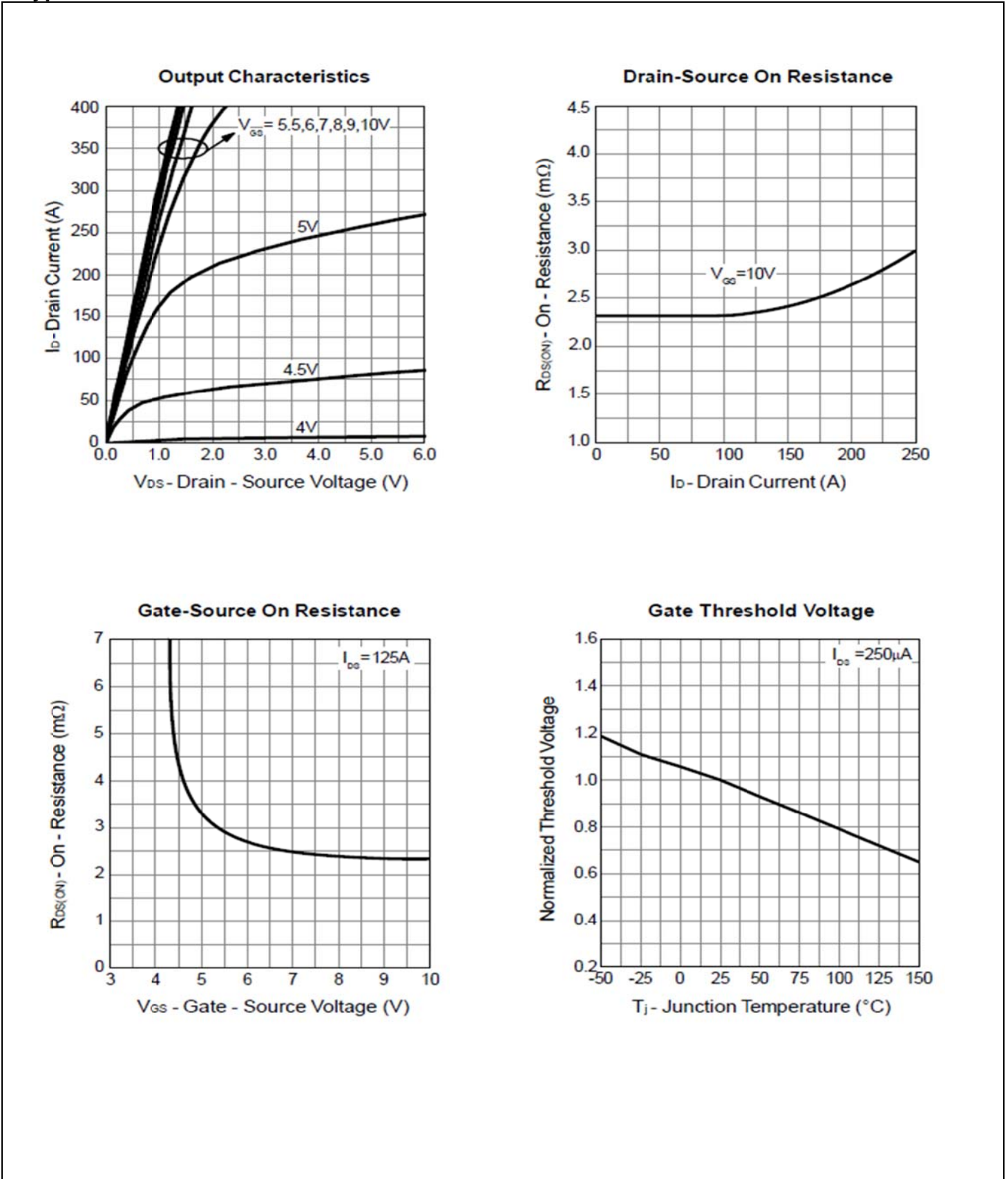
2: Guaranteed by design, not subject to production testing.

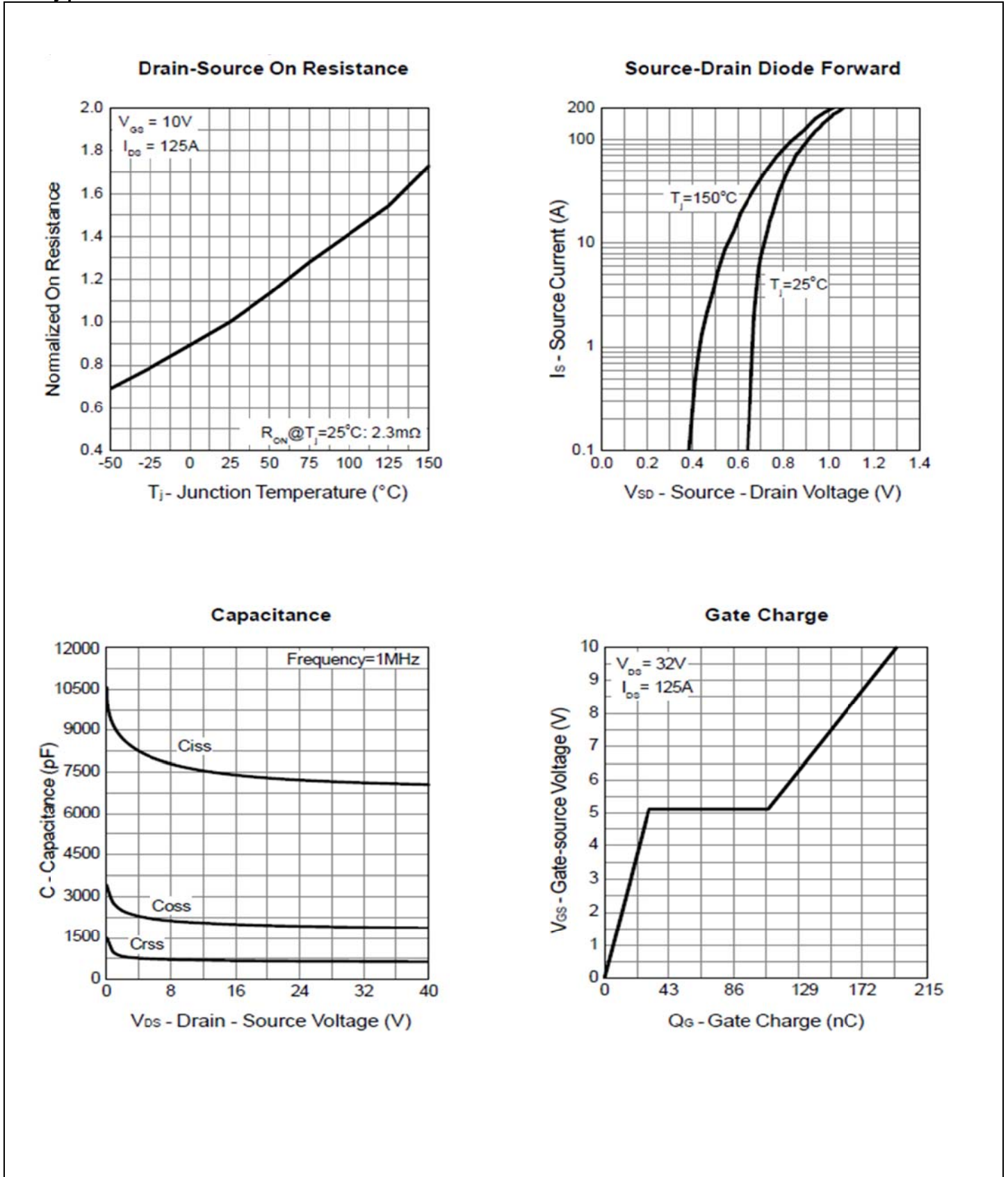
3: Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 55A.

4: Repetitive rating, pulse width limited by max junction temperature.

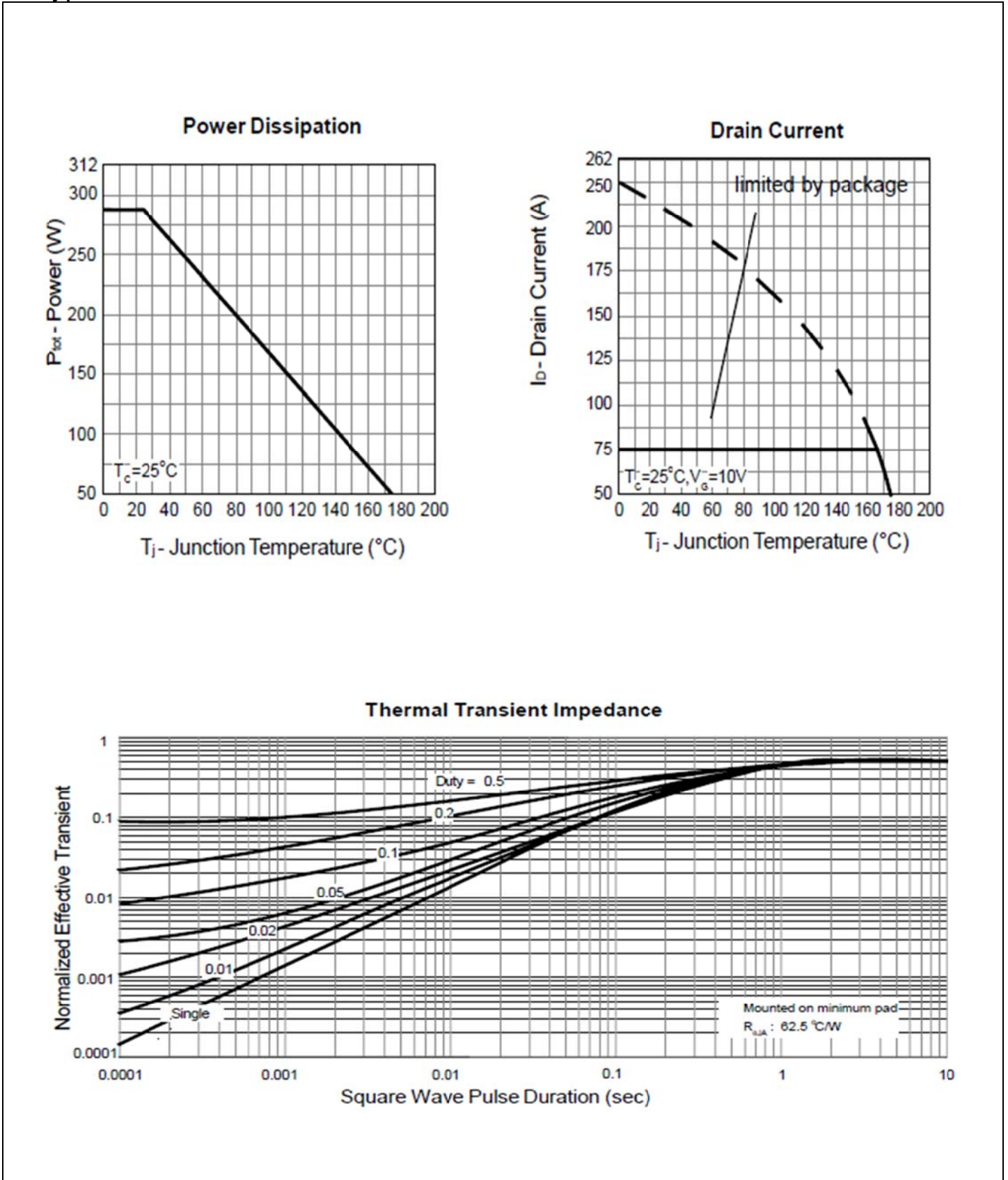
5: Starting T<sub>J</sub> = 25°C, L = 1mH

**Typical Characteristics**



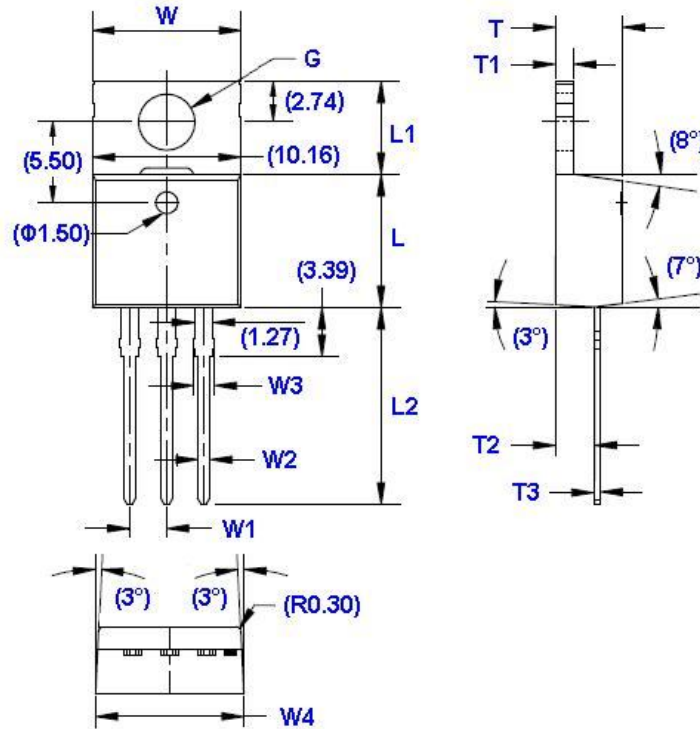
**Typical Characteristics (Continued)**


Typical Characteristics (Continued)



**Package Dimension**
**TO-220W**

Unit: mm



Symbol	Size		Symbol	Size		Symbol	Size	
	Min	Max		Min	Max		Min	Max
W	10.00	10.40	L	8.86	9.26	T2	2.46	2.86
W1	2.54 (TYP)		L1	6.09	6.49	T3	0.28	0.48
W2	0.71	0.91	L2	13.25	13.65	G ( $\Phi$ )	3.73	3.93
W3	1.14	1.54	T	4.40	4.80			
W4	9.96	10.36	T1	1.14	1.40			